Preferred Device

Darlington Transistor NPN Silicon

Features

• Pb–Free Package is Available

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector – Emitter Voltage	V _{CEO}	40	Vdc
Collector-Base Voltage	V _{CBO}	40	Vdc
Emitter-Base Voltage	V _{EBO}	12	Vdc
Collector Current – Continuous	Ι _C	500	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR–5 Board, (Note 1) T _A = 25°C Derate above 25°C	PD	225 1.8	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	556	°C/W
Total Device Dissipation Alumina Substrate, (Note 2) $T_A = 25^{\circ}C$ Derate above $25^{\circ}C$	PD	300 2.4	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	417	°C/W
Junction and Storage Temperature	T _J , T _{stg}	-55 to +150	°C

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

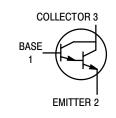
1. $FR-5 = 1.0 \times 0.75 \times 0.062$ in.

2. Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.



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SOT-23 (TO-236) CASE 318 STYLE 6

MARKING DIAGRAM



1V = Device Code

M = Date Code*

= Pb–Free Package

(Note: Microdot may be in either location) *Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping [†]
MMBT6427LT1	SOT-23	3,000 / Tape & Reel
MMBT6427LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

Preferred devices are recommended choices for future use and best overall value.

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector – Emitter Breakdown Voltage $(I_C = 10 \text{ mAdc}, V_{BE} = 0)$	V _{(BR)CEO}	40	_	Vdc
Collector – Base Breakdown Voltage $(I_C = 100 \ \mu Adc, I_E = 0)$	V _{(BR)CBO}	40	_	Vdc
Emitter – Base Breakdown Voltage ($I_C = 10 \ \mu Adc, I_C = 0$)	V _{(BR)EBO}	12	_	Vdc
Collector Cutoff Current $(V_{CE} = 25 \text{ Vdc}, I_B = 0)$	I _{CES}	_	1.0	μAdc
Collector Cutoff Current ($V_{CB} = 30 \text{ Vdc}, I_E = 0$)	Ісво	_	50	nAdc
Emitter Cutoff Current ($V_{EB} = 10 \text{ Vdc}, I_C = 0$)	I _{EBO}	_	50	nAdc
ON CHARACTERISTICS	·			
DC Current Gain ($I_C = 10 \text{ mAdc}, V_{CE} = 5.0 \text{ Vdc}$) ($I_C = 100 \text{ mAdc}, V_{CE} = 5.0 \text{ Vdc}$) ($I_C = 500 \text{ mAdc}, V_{CE} = 5.0 \text{ Vdc}$)	h _{FE}	10,000 20,000 14,000	100,000 200,000 140,000	-
Collector – Emitter Saturation Voltage $(I_C = 50 \text{ mAdc}, I_B = 0.5 \text{ mAdc})$ $(I_C = 500 \text{ mAdc}, I_B = 0.5 \text{ mAdc})$	V _{CE(sat)} ⁽³⁾		1.2 1.5	Vdc
Base – Emitter Saturation Voltage ($I_C = 500 \text{ mAdc}, I_B = 0.5 \text{ mAdc}$)	V _{BE(sat)}	_	2.0	Vdc
Base – Emitter On Voltage ($I_C = 50 \text{ mAdc}, V_{CE} = 5.0 \text{ Vdc}$)	V _{BE(on)}	_	1.75	Vdc
SMALL-SIGNAL CHARACTERISTICS	·			
Output Capacitance ($V_{CB} = 10 \text{ Vdc}, I_E = 0, f = 1.0 \text{ MHz}$)	C _{obo}	_	7.0	pF
Input Capacitance ($V_{EB} = 0.5 \text{ Vdc}, I_C = 0, f = 1.0 \text{ MHz}$)	C _{ibo}	_	15	pF
Current Gain – High Frequency ($I_C = 10$ mAdc, $V_{CE} = 5.0$ Vdc, f = 100 MHz)	h _{fe}	1.3	-	Vdc
Noise Figure (I _C = 1.0 mAdc, V _{CE} = 5.0 Vdc, R _S = 100 k Ω , f = 1.0 kHz)	NF	_	10	dB

3. Pulse Test: Pulse Width = $300 \ \mu$ s, Duty Cycle = 2.0%.

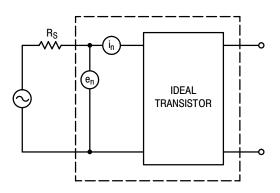


Figure 1. Transistor Noise Model

NOISE CHARACTERISTICS

 $(V_{CE}=5.0~Vdc,~T_{A}=25^{\circ}C)$

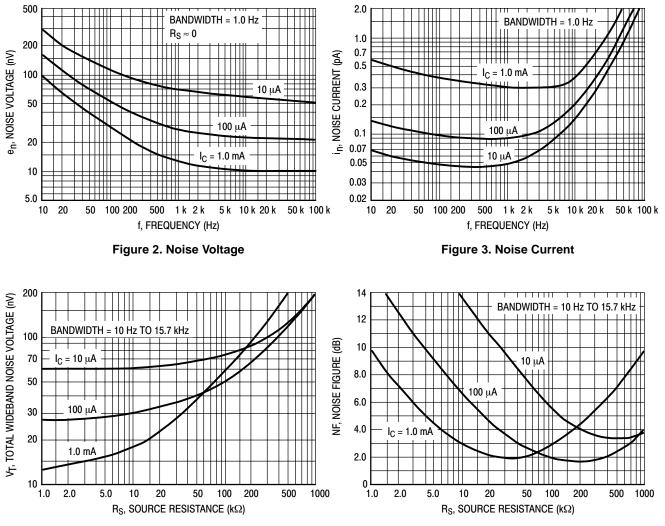
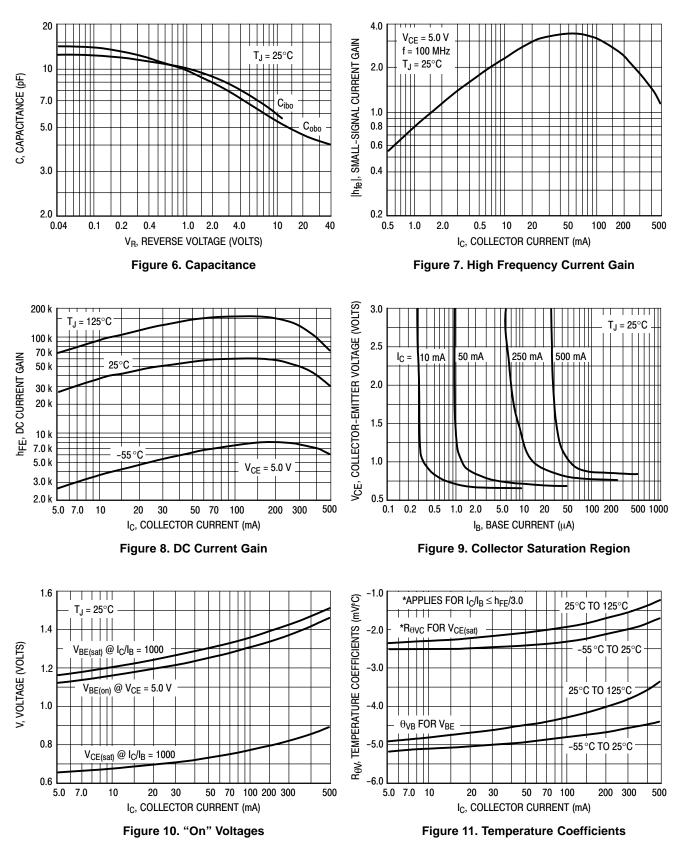
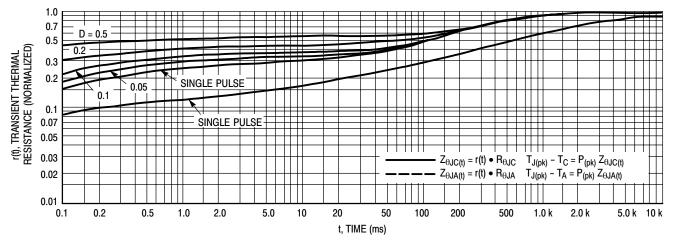


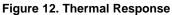
Figure 4. Total Wideband Noise Voltage

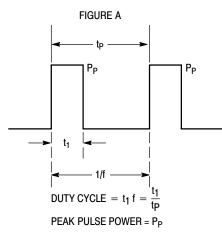
Figure 5. Wideband Noise Figure







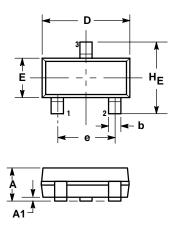


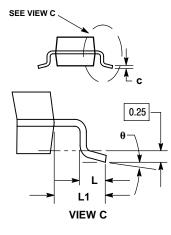




PACKAGE DIMENSIONS

SOT-23 (TO-236) CASE 318-08 **ISSUE AN**





NOTES

- DIMENSIONING AND TOLERANCING PER ANSI 1. Y14.5M, 1982. CONTROLLING DIMENSION: INCH
- 2. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF 3.
- BASE MATERIAL. 318-01 THRU -07 AND -09 OBSOLETE, NEW STANDARD 318-08. 4

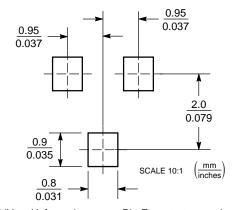
	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.89	1.00	1.11	0.035	0.040	0.044
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.37	0.44	0.50	0.015	0.018	0.020
С	0.09	0.13	0.18	0.003	0.005	0.007
D	2.80	2.90	3.04	0.110	0.114	0.120
Е	1.20	1.30	1.40	0.047	0.051	0.055
е	1.78	1.90	2.04	0.070	0.075	0.081
L	0.10	0.20	0.30	0.004	0.008	0.012
L1	0.35	0.54	0.69	0.014	0.021	0.029
HE	2.10	2.40	2.64	0.083	0.094	0.104

STYLE 6:

PIN 1. BASE 2. EMITTER

3. COLLECTOR

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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